

FDMQ8203

GreenBridge™ Series of High-Efficiency Bridge Rectifiers Dual N-Channel and Dual P-Channel PowerTrench® MOSFET

N-Channel: 100 V, 6 A, 110 mΩ P-Channel: -80 V, -6 A, 190 mΩ

Features

Q1/Q4: N-Channel

- Max $r_{DS(on)}$ = 110 mΩ at $V_{GS} = 10$ V, $I_D = 3$ A
- Max $r_{DS(on)}$ = 175 mΩ at $V_{GS} = 6$ V, $I_D = 2.4$ A

Q2/Q3: P-Channel

- Max $r_{DS(on)}$ = 190 mΩ at $V_{GS} = -10$ V, $I_D = -2.3$ A
- Max $r_{DS(on)}$ = 235 mΩ at $V_{GS} = -4.5$ V, $I_D = -2.1$ A
- Substantial efficiency benefit in PD solutions
- RoHS Compliant

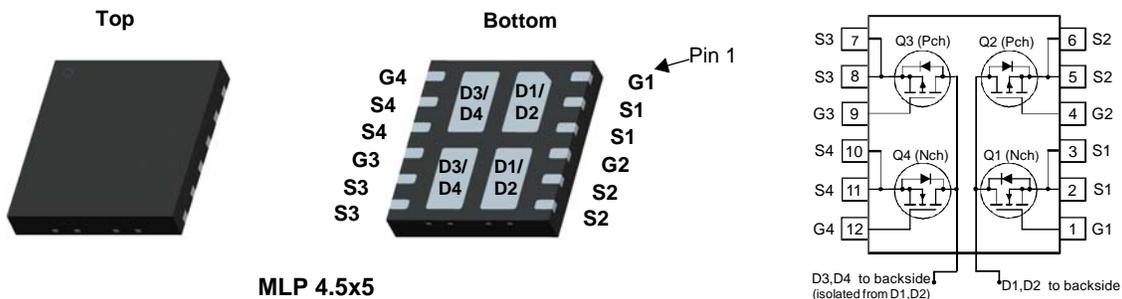


General Description

This quad mosfet solution provides ten-fold improvement in power dissipation over diode bridge.

Application

- High-Efficiency Bridge Rectifiers



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Q1/Q4	Q2/Q3	Units
V_{DS}	Drain to Source Voltage	100	-80	V
V_{GS}	Gate to Source Voltage	± 20	± 20	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	6	-6	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	10	-10	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	3.4	-2.6	
	-Pulsed	12	-10	
P_D	Power Dissipation for Single Operation $T_C = 25^\circ\text{C}$	22	37	W
	Power Dissipation for Dual Operation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5		
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	160	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMQ8203	FDMQ8203	MLP4.5x5	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$ $I_D = -250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$	Q1/Q4 Q2/Q3	100 -80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ $I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$	Q1/Q4 Q2/Q3		72 -79		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = -64\text{ V}, V_{GS} = 0\text{ V}$	Q1/Q4 Q2/Q3			1 -1	μA μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	Q1/Q4 Q2/Q3			± 100 ± 100	nA nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ $V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	Q1/Q4 Q2/Q3	2 -1	3 -1.6	4 -3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ $I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$	Q1/Q4 Q2/Q3		-8 5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 3\text{ A}$ $V_{GS} = 6\text{ V}, I_D = 2.4\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 3\text{ A}, T_J = 125\text{ }^\circ\text{C}$ $V_{GS} = -10\text{ V}, I_D = -2.3\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -2.1\text{ A}$ $V_{GS} = -10\text{ V}, I_D = -2.3\text{ A}, T_J = 125\text{ }^\circ\text{C}$	Q1/Q4 Q2/Q3		85 118 147 161 188 273	110 175 191 190 235 323	$m\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 3\text{ A}$ $V_{DS} = -10\text{ V}, I_D = -2.3\text{ A}$	Q1/Q4 Q2/Q3		6 6		S

Dynamic Characteristics

C_{iss}	Input Capacitance	Q1/Q4: $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Q1/Q4 Q2/Q3		158 639	210 850	pF
C_{oss}	Output Capacitance	Q2/Q3:	Q1/Q4 Q2/Q3		41 46	55 65	pF
C_{rss}	Reverse Transfer Capacitance	$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Q1/Q4 Q2/Q3		2.6 24	5 40	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	Q1/Q4:	Q1/Q4 Q2/Q3		3.8 4.7	10 10	ns
t_r	Rise Time	$V_{DD} = 50\text{ V}, I_D = 3\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$	Q1/Q4 Q2/Q3		1.3 2.8	10 10	ns
$t_{d(off)}$	Turn-Off Delay Time	Q2/Q3:	Q1/Q4 Q2/Q3		7.5 22	15 35	ns
t_f	Fall Time	$V_{DD} = -40\text{ V}, I_D = -2.3\text{ A},$ $V_{GS} = -10\text{ V}, R_{GEN} = 6\text{ }\Omega$	Q1/Q4 Q2/Q3		1.9 2.7	10 10	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$ $V_{GS} = 0\text{ V to }-10\text{ V}$	Q1/Q4: Q2/Q3		2.9 13	5 19	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to }5\text{ V}$ $V_{GS} = 0\text{ V to }-4.5\text{ V}$	$V_{DD} = 50\text{ V},$ $I_D = 3\text{ A}$ Q1/Q4 Q2/Q3		1.6 6.4	3 10	nC
Q_{gs}	Gate to Source Gate Charge	Q2/Q3: $V_{DD} = -40\text{ V},$ $I_D = -2.3\text{ A}$	Q1/Q4 Q2/Q3		0.8 1.6		nC
Q_{gd}	Gate to Drain "Miller" Charge		Q1/Q4 Q2/Q3		0.8 2.6		nC

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Drain-Source Diode Characteristics							
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3\text{ A}$ (Note 2)	Q1/Q4		0.86	1.3	V
		$V_{GS} = 0\text{ V}, I_S = -2.3\text{ A}$ (Note 2)	Q2/Q3		-0.82	-1.3	
t_{rr}	Reverse Recovery Time	Q1/Q4: $I_F = 3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Q1/Q4		32	52	ns
			Q2/Q3		26	42	
Q_{rr}	Reverse Recovery Charge	$I_F = -2.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Q1/Q4		21	34	nC
			Q2/Q3		26	42	

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 50 °C/W when mounted on a 1 in² pad of 2 oz copper, the board designed Q1+Q3 or Q2+Q4.



b. 160 °C/W when mounted on a minimum pad of 2 oz copper, the board designed Q1+Q3 or Q2+Q4.

2: Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

Typical Characteristics (N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

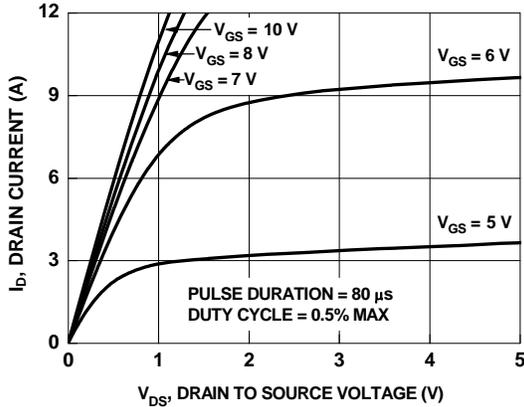


Figure 1. On Region Characteristics

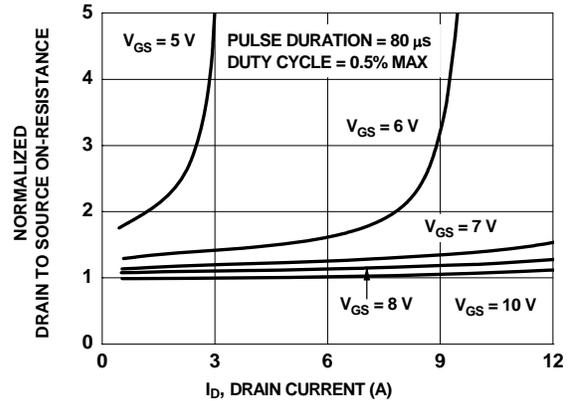


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

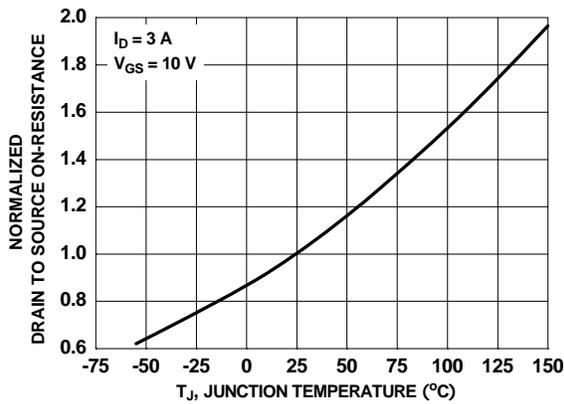


Figure 3. Normalized On Resistance vs Junction Temperature

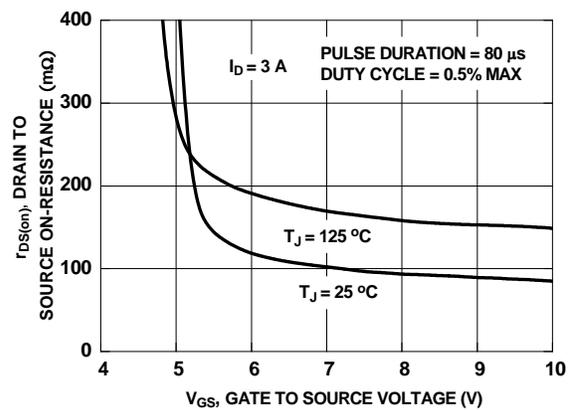


Figure 4. On-Resistance vs Gate to Source Voltage

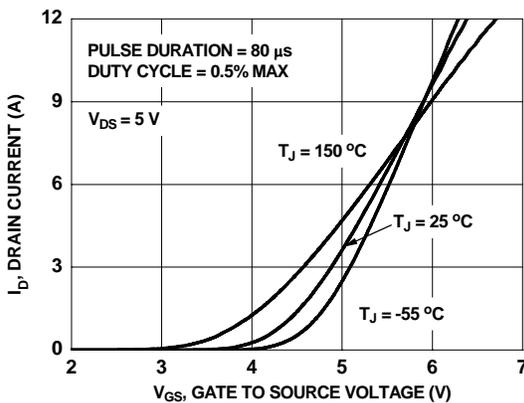


Figure 5. Transfer Characteristics

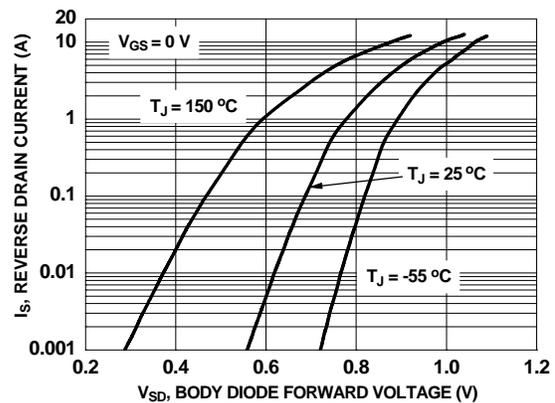


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (N-Channel) $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

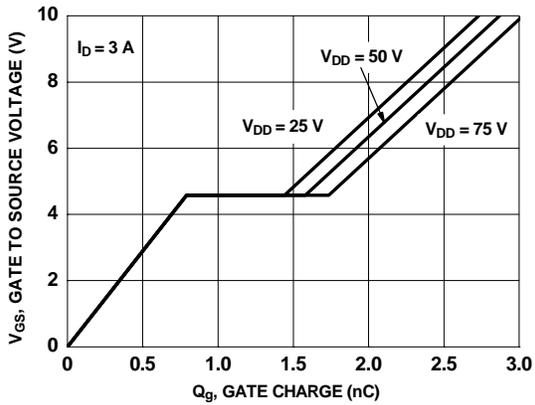


Figure 7. Gate Charge Characteristics

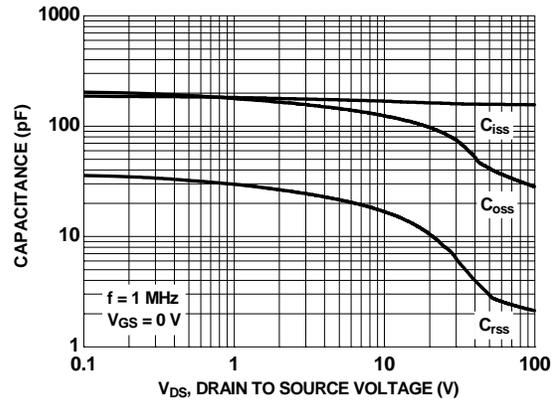


Figure 8. Capacitance vs Drain to Source Voltage

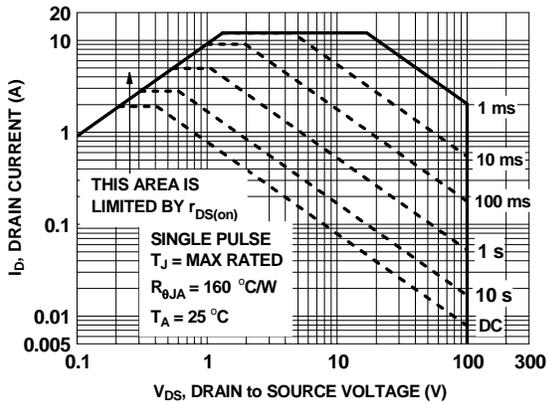


Figure 9. Forward Bias Safe Operating Area

Typical Characteristics (P-Channel) $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

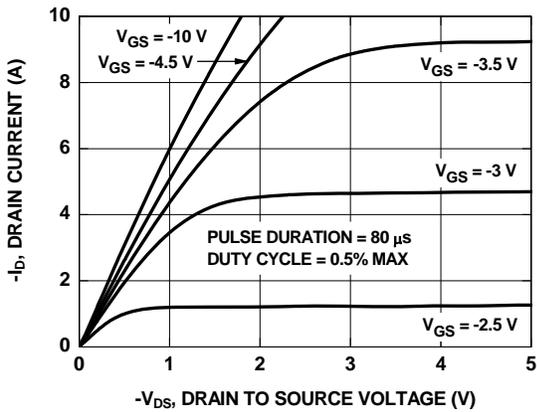


Figure 10. On-Region Characteristics

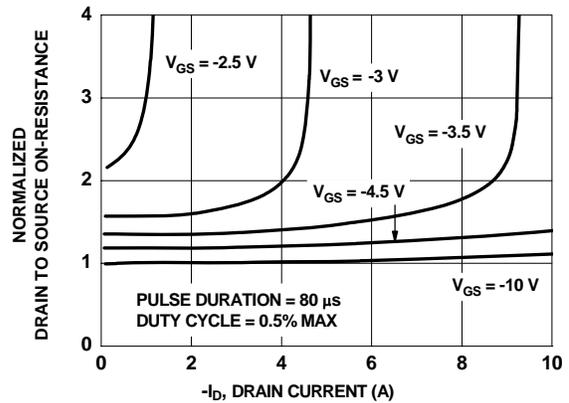


Figure 11. Normalized on-Resistance vs Drain Current and Gate Voltage

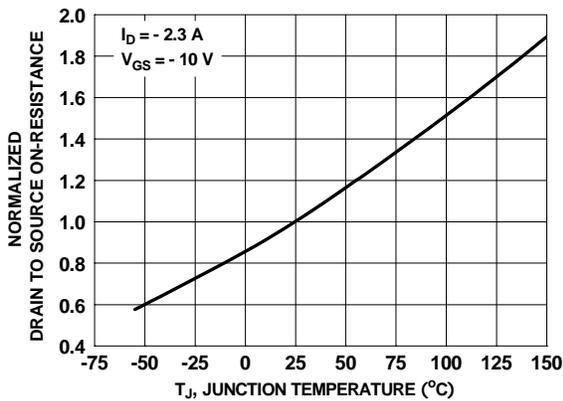


Figure 12. Normalized On-Resistance vs Junction Temperature

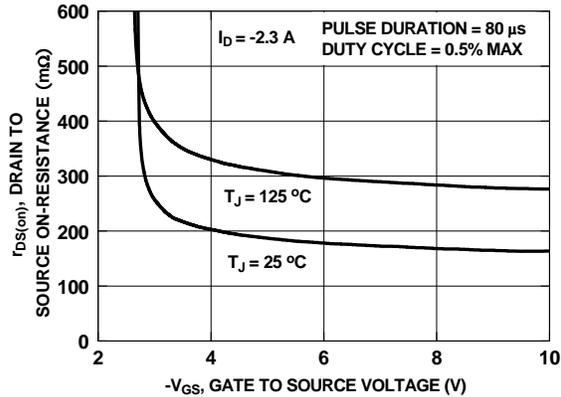


Figure 13. On-Resistance vs Gate to Source Voltage

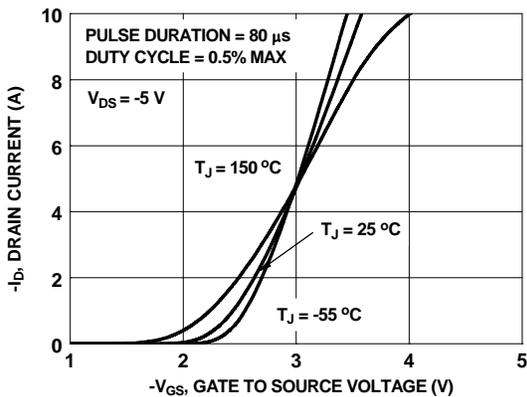


Figure 14. Transfer Characteristics

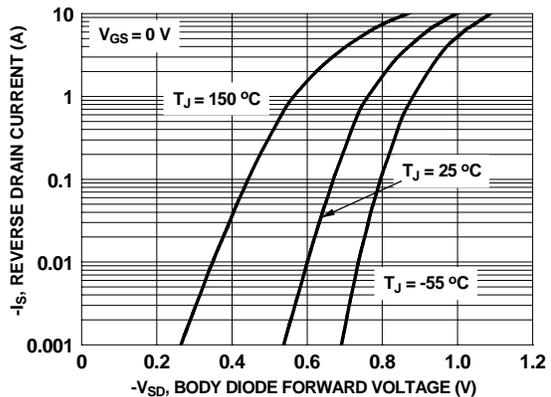


Figure 15. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (P-Channel) $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

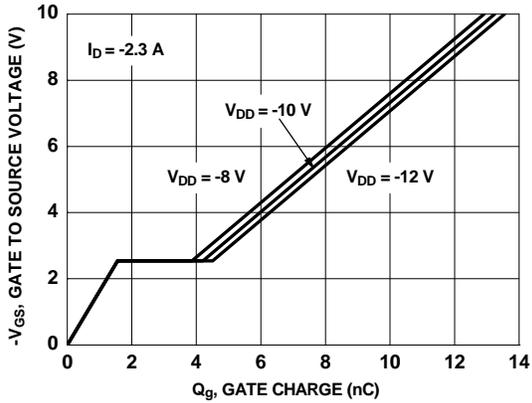


Figure 16. Gate Charge Characteristics

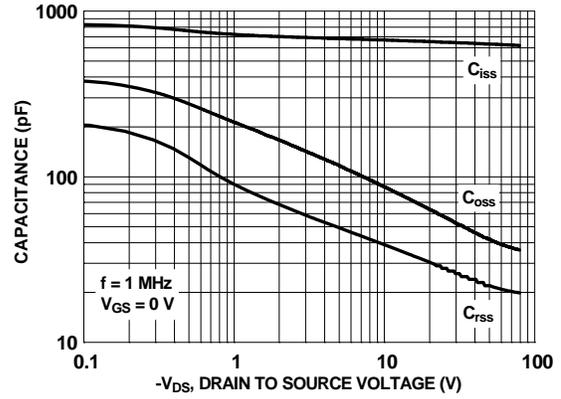


Figure 17. Capacitance vs Drain to Source Voltage

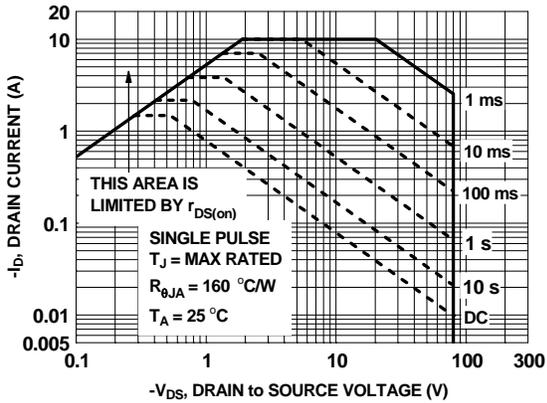


Figure 18. Forward Bias Safe Operating Area

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

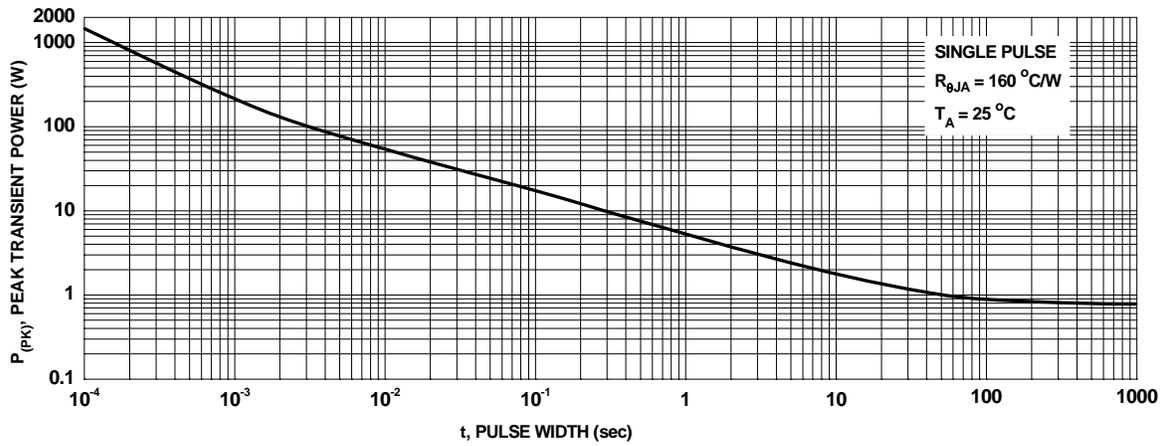


Figure 19. Single Pulse Maximum Power Dissipation

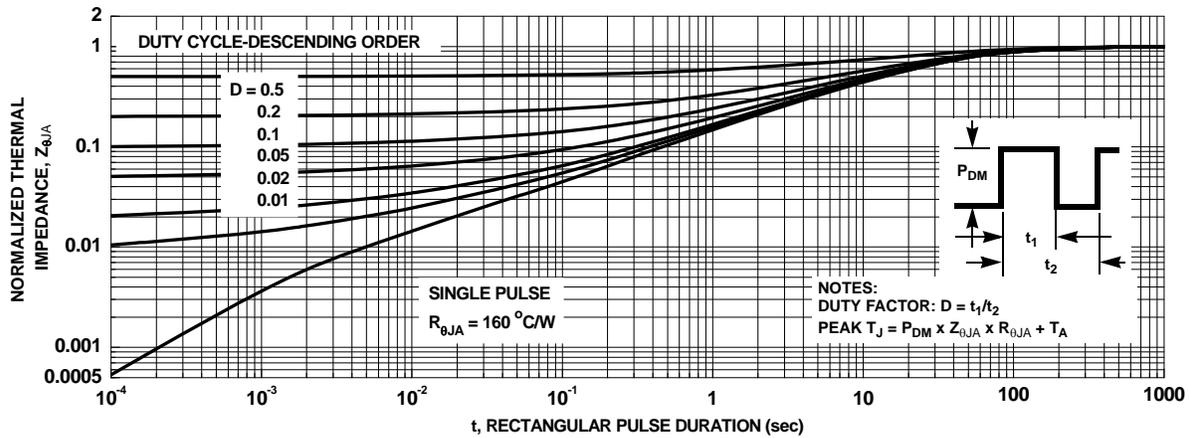
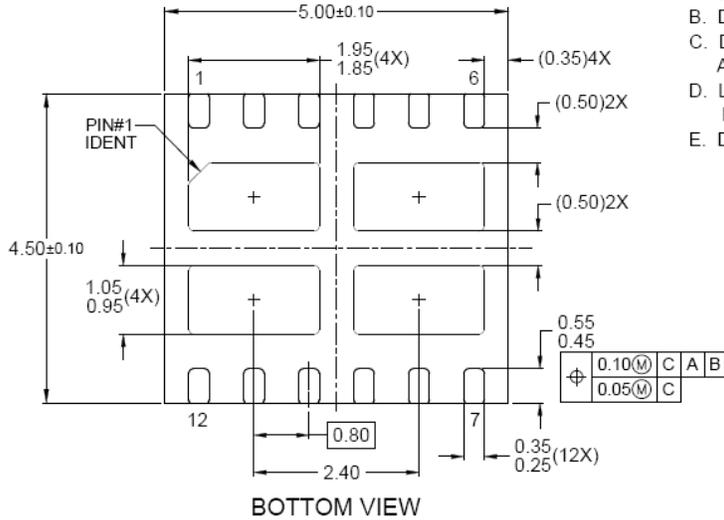
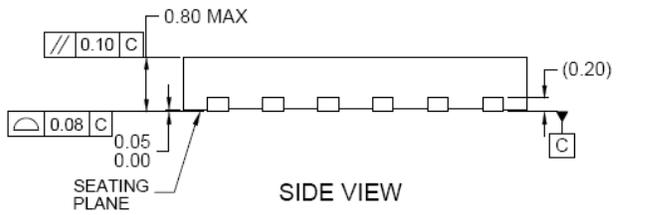
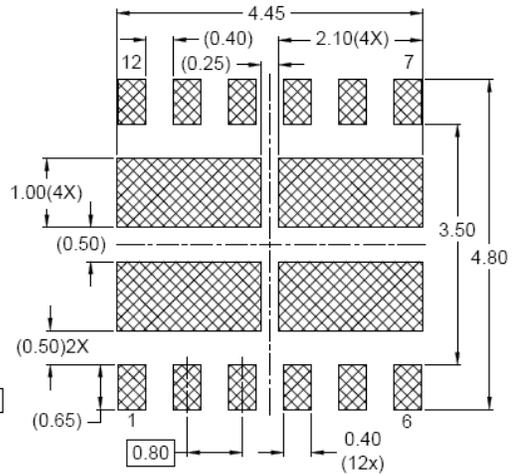
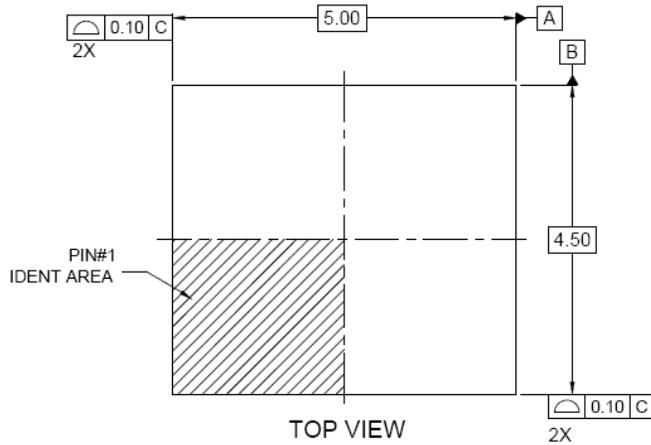


Figure 20. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout



NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.
- E. DRAWING FILENAME: MKT-MLP12Erev2.



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Definition of Terms

Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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